

IN THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A method of forming a metal line layer in a semiconductor device, comprising:

depositing ~~a metal line layer having~~ first, second and third conductive layers on a semiconductor substrate;

depositing an insulating film on the third conductive layer;

depositing and patterning a photosensitive material on the insulating film;

etching portions of the insulating film, the third and second conductive layers using the photosensitive material as a mask;

removing the photosensitive material;

forming a side wall oxide film on the side walls of the second conductive layer; and

etching portions of the first conductive layer using the insulating film as a hard mask.

2. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the second conductive layer is made of aluminum (Al).

3. (Previously Presented) A method of forming a metal line layer in a semiconductor device according to claim 1, wherein the metal line layer is formed by laminating a first Ti/TiN layer, an Al layer and a second Ti/TiN layer in this order, and the side wall oxide film is an Al_2O_3 film.

4. (Previously Presented) A method of forming a metal line in a semiconductor memory device according to claim 1, wherein the insulating film, the third and second conductive layers are dry-etched using activated plasma comprising $\text{Cl}_2/\text{BCl}_3/\text{N}_2$ gas.

5. (Canceled)

6. (Previously Presented) A method of forming a metal line in a semiconductor device according to claim 1, wherein the insulating film is a nitride film.

7. (Currently Amended) A method of forming a metal line in a semiconductor device according to claim 1, wherein the

insulating film is etched by means of a dry etching process using activated plasma comprising a combination of $\text{CHF}_3/\text{CF}_4/\text{Ar}$ or C_xF_y (where x, y are natural numbers)/ O_2/Ar gas.

8. (Canceled)